

Features

- Epitaxial Planar Die Construction ٠
- Ideal for Low Power Amplification and Switching .
- Complementary PNP Type Available (DSS5240Y)
- Ultra Small Surface Mount Package
- "Lead Free", RoHS Compliant (Note 1)
- Halogen and Antimony Free "Green" Device (Note 2)
- ESD rating: 400V-MM, 8KV-HBM
- Qualified to AEC-Q101 Standards for High Reliability

Mechanical Data

- Case: SOT363 ٠
- Case Material: Molded Plastic, "Green" Molding Compound. • UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin annealed over Copper Plated Alloy 42 leadframe. Solderable per MIL-STD-202, Method 208
- Weight: 0.006 grams (approximate)

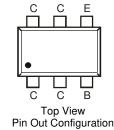


SOT363

Top View



Device Schematic



Ordering Information (Note 3)

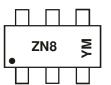
Product	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
DSS4240Y-7	ZN8	7	8mm	3,000

Notes:

No purposefully added lead.
Diode's Inc.'s "Green" policy can be found on our website at http://www.diodes.com.

3. For packaging details, go to our website at http://www.diodes.com.

Marking Information



ZN8 = Product Type Marking Code YM = Date Code Marking Y = Year (ex: V = 2008)M = Month (ex: 9 = September)

Date Code Kev

Year	20	10	20	11	20	12	20	13	20	14	20	15
Code	>	<	١	(2	<u>Z</u>	ŀ	4	E	3	()
Month	Jan	Feb	Mar	Apr	Мау	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D



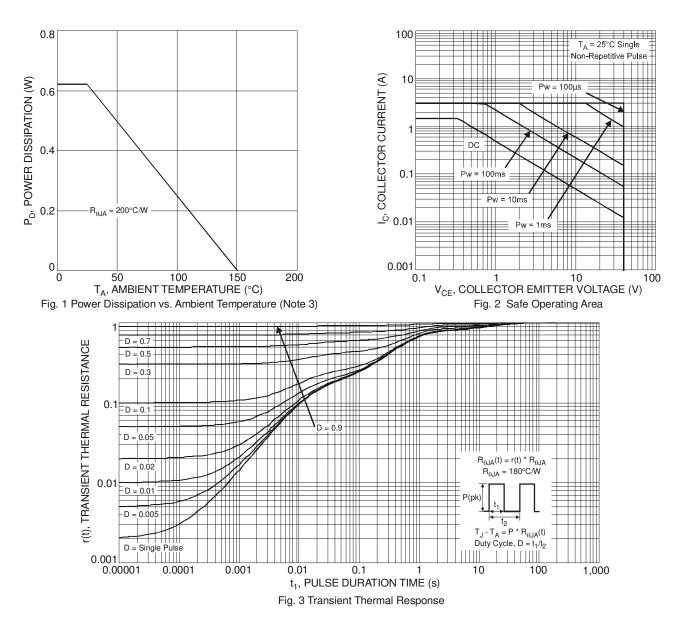
Maximum Ratings @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V _{CBO}	40	V
Collector-Emitter Voltage	V _{CEO}	40	V
Emitter-Base Voltage	V _{EBO}	5	V
Collector Current - Continuous	Ic	2	A
Peak Pulse Collector Current	ICM	3	A
Peak Base Current	I _{BM}	0.3	A

Thermal Characteristics

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 4) @ $T_A = 25^{\circ}C$	PD	625	mW
Thermal Resistance, Junction to Ambient (Note 4) @ T _A = 25°C	R _{0JA}	200	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	۵°

Notes: 4. Device mounted on FR-4 PCB, with minimum recommended pad layout.

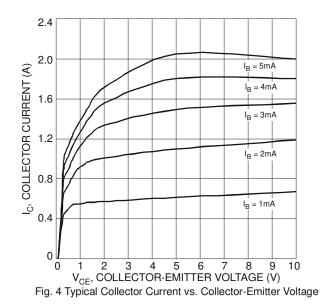


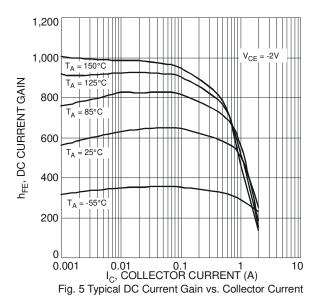


Electrical Characteristics @T_A = 25°C unless otherwise specified

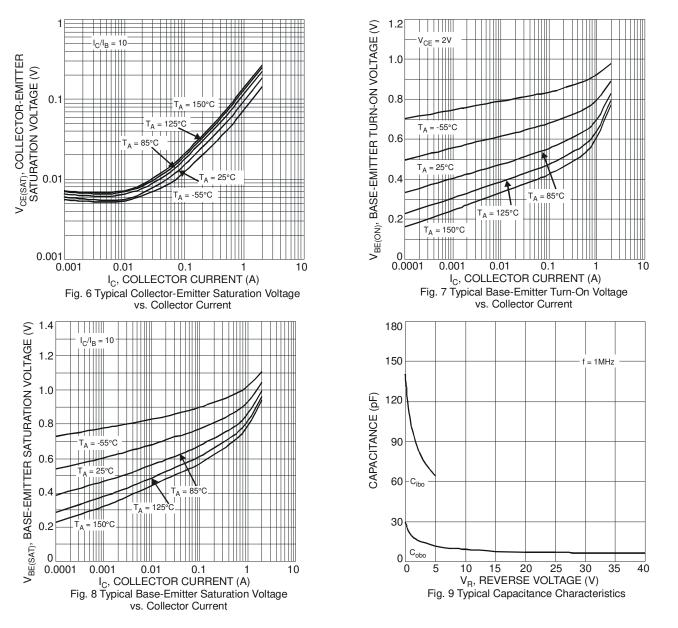
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Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	BV _{CBO}	40	150		V	$I_{\rm C} = 100 \mu A, I_{\rm E} = 0$
Collector-Emitter Breakdown Voltage (Note 5)	BV _{CEO}	40	55	_	V	$I_{C} = 10 \text{mA}, I_{B} = 0$
Emitter-Base Breakdown Voltage	BV _{EBO}	5	8.5	_	V	$I_E = 100 \mu A, I_C = 0$
Collector Cutoff Current	I _{CBO}	_		100	nA	$V_{CB} = 30V, I_E = 0$
		—	—	50	μA	$V_{CB} = 30V, I_E = 0, T_A = 150^{\circ}C$
Emitter Cutoff Current	I _{EBO}			100	nA	$V_{EB} = 4V, I_C = 0$
		350	_	_		$V_{CE} = 2V, I_{C} = 100 \text{mA}$
DC Current Gain (Note 5)	h	300		_		$V_{CE} = 2V, I_{C} = 500 \text{mA}$
Do Guneni Gain (Note 5)	h _{FE}	300	—	_	_	$V_{CE} = 2V, I_C = 1A$
		150		_		$V_{CE} = 2V, I_C = 2A$
	V _{CE(sat)}		45	70	mV	$I_{C} = 100 \text{mA}, I_{B} = 1 \text{mA}$
			52	100		$I_{C} = 500 \text{mA}, I_{B} = 50 \text{mA}$
Collector-Emitter Saturation Voltage (Note 5)		_	100	180		I _C = 750mA, I _B = 15mA
			105	180		$I_{C} = 1A$, $I_{B} = 50mA$
		—	190	320		$I_{C} = 2A, I_{B} = 200 mA$
Collector-Emitter Saturation Resistance	R _{CE(sat)}	—	105	200	mΩ	$I_{C} = 500 \text{mA}, I_{B} = 50 \text{mA}$
Base-Emitter Saturation Voltage	V _{BE(sat)}	_		1.1	V	$I_{C} = 2A, I_{B} = 200 mA$
Base-Emitter Turn On Voltage	V _{BE(on)}	—	_	0.75	V	$V_{CE} = 2V, I_{C} = 100 \text{mA}$
Output Capacitance	C _{obo}	_	_	20	pF	V _{CB} = 10V, f = 1.0MHz
Current Gain-Bandwidth Product	f⊤	100	250		MHz	$V_{CE} = 10V, I_C = 50mA, f = 100MHz$
Turn-On Time	t _{on}	_	64	_	ns	
Delay Time	td	_	20	_	ns	
Rise Time	tr	_	44	_	ns	$V_{CC} = 10V$
Turn-Off Time	t _{off}		315		ns	$I_{C} = 1A, I_{B1} = -I_{B2} = 50mA$
Storage Time	ts		275		ns]
Fall Time	t _f	—	40		ns]

Notes: 5. Measured under pulsed conditions. Pulse width = 300μ s. Duty cycle $\leq 2\%$.

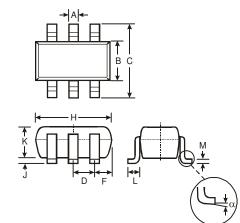








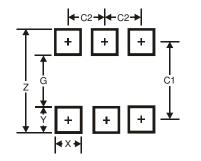
Package Outline Dimensions



SOT363					
Dim	Min	Max			
Α	0.10	0.30			
В	1.15	1.35			
С	2.00	2.20			
D	0.65	0.65 Typ			
F	0.40	0.45			
Н	1.80	2.20			
J	0	0.10			
К	0.90	1.00			
L	0.25	0.40			
Μ	0.10	0.22			
α	0°	8°			
All Dimensions in mm					



Suggested Pad Layout



Dimensions	Value (in mm)
Z	2.5
G	1.3
Х	0.42
Y	0.6
C1	1.9
C2	0.65

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